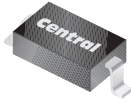




**CMDSH-3**  
**SURFACE MOUNT**  
**SILICON SCHOTTKY DIODE**

**SUPERmini™**



**SOD-323 CASE**

• Device is **Halogen Free** by Design



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMDSH-3 type is a silicon Schottky diode, manufactured in a SUPERmini™ surface mount package, designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: S1**

**MAXIMUM RATINGS:** (T<sub>A</sub>=25°C unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	30	V
Average Forward Current	I <sub>O</sub>	100	mA
Peak Forward Surge Current, tp=10ms	I <sub>FSM</sub>	750	mA
Power Dissipation	P <sub>D</sub>	250	mW
Power Dissipation (T <sub>L</sub> =25°C)	P <sub>D</sub>	833	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	500	°C/W
Thermal Resistance	θ <sub>JL</sub>	150	°C/W

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C)

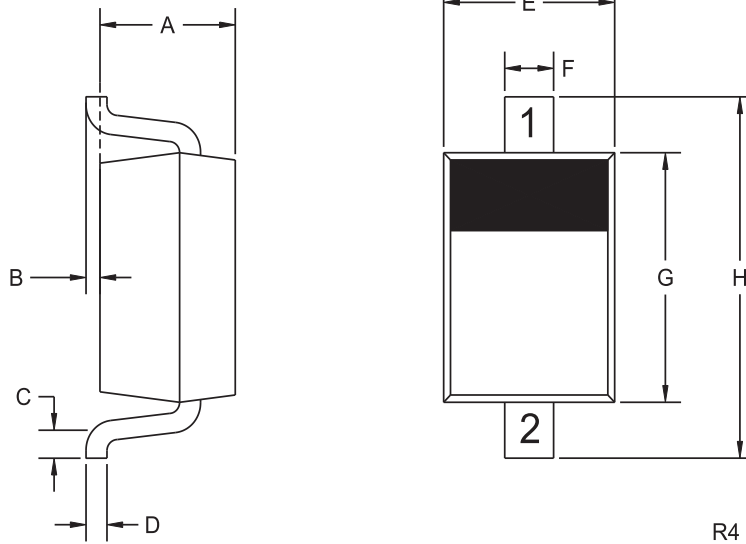
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =25V			1.0	μA
BV <sub>R</sub>	I <sub>F</sub> =100μA	30			V
V <sub>F</sub>	I <sub>F</sub> =2.0mA		0.30		V
V <sub>F</sub>	I <sub>F</sub> =15mA		0.36		V
V <sub>F</sub>	I <sub>F</sub> =50mA		0.47	0.55	V
V <sub>F</sub>	I <sub>F</sub> =100mA		0.58	0.80	V
C <sub>J</sub>	V <sub>R</sub> =10V, f=1.0MHz		7.0		pF



**CMDSH-3**  
**SURFACE MOUNT**  
**SILICON SCHOTTKY DIODE**



**SOD-323 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Cathode
- 2) Anode

**MARKING CODE: S1**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R8 (24-July 2012)